4K × 9-Bit CMOS Parallel In-Out FIFO Memory

■ DESCRIPTION

The HM63941 is a First-In, First-Out memory that utilizes a high performance static RAM array with internal algorithm that controls, monitors and declares status of the memory by empty flag, full flag and almost-full flag, to prevent data overflow or underflow.

Expansion logic warrants unlimited expansion capability in width and depth. Both read and write are independent from each other and their corresponding pointers are designed to select the proper locations out of the entire array serially without address information to load or unload data.

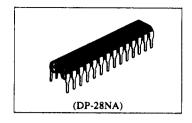
Data is toggled in and out of the device through the use of the write enable (\overline{W}) and read enable (\overline{R}) pins. The device has a read/write cycle time of 35/45/60ns. Organization of HM63941 provides a 9-bit data bus. the ninth bit could be used for control or parity for error checking at the option of the user. The HM63941 is fabricated using the Hitachi CMOS 1.3micron technology. The device is available in DIP.

■ FEATURES

- First-In, First-Out Dual Port Memory
- 4k × 9 Organization
- Low-Power CMOS 1.3micron Technology
- Asynchronous and Simultaneous Read and Write
- · Fully Expandable in Depth and/or Width
- Single 5V (± 10%) Power Supply
- Empty and Full Warning Flags
- Almost-Full Flag

ORDERING INFORMATION

Type Name	Access Time	Package
HM63941P-25	25ns	
HM63941P-35	35ns	28-pin Plastic DIP
HM63941P-45	45ns	•



■ PIN ARRANGEMENT

i .			_
₩ 🗆	1	28	□ Vcc
D8 🗆	2	27	□ D4
D3 🗌	3	26	D ₅
D2 🗌	4	25	□ D ₆
D1 🗆	5	24	□ D ₇
□ □	6	23	☐ FL/RT
X1 🗀	7	22	_ RS
FF [8	21	EF
Q₀ [9	20	XO/AF
Q1 [10	19	☐ Q ₇
Q2 [11	18	□ Q ₆
Q3 [12	17	Q ₅
Q8 [13	16	Q₄
Vss 🗌	14	15	Ā
			'
	(Top	View)	

■ PIN DESCRIPTION

Pin Name	Function
$D_{0}-D_{8}$	Data inputs
RS	Reset
$\overline{\mathbf{w}}$	Write enable
R	Read enable
FL	First load
RT	Retransmit
Xī	Expansion-in
XÖ	Expansion-out
ĀĒ	Almost-full flag
FF	Full flag
ĒF	Empty flag
$Q_0 - Q_8$	Data outputs

■ ABSOLUTE MAXIMUM RATINGS

Item	Symbol	Rating	Unit
Terminal Voltage(1)	V _T	$-0.5^{(2)}$ to $+7.0$	V
Power Dissipation	P _T	1.0	W
Operating Temperature	Topr	0 to +70	°C
Storage Temperature	T _{stg}	-55 to +125	°C
Storage Temperature Under Bias	T _{bias}	-10 to +85	°C

NOTES:

- 1. Relative to Vss.
- 2. -3.5V for pulse width \leq 10ns.

■ ELECTRICAL CHARACTERISTICS

• Recommended DC Operating Conditions ($T_a = 0 \text{ to } +70^{\circ}\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Supply Voltage	v _{cc}	4.5	5.0	5.5	V
	V _{SS}	0	0	0	V
	V _{IH}	2.0		6.0	V
Input Voltage	V _{IL}	-0.5(1)	_	0.8	V

NOTE: 1. -3.0V for pulse width \leq 10ns.

DC CHARACTERISTICS ($T_a = 0$ °C to +70°C, $V_{CC} = 5V \pm 10\%$)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Input Leakage Current	I _{LI}	$V_{CC} = 5.5V, V_{in} = 0V - V_{CC}$	1 -	_	2	μA
Output Leakage Current	I _{LO}	$\overline{R} = V_{IH}, V_{out} = 0V - V_{CC}$	T -	_	2	μΑ
	I _{CC1}	Average Operating Current		_	80	mA
Operating Power Supply Current	l_{CC2}	$\overline{R} = \overline{W} = \overline{RS} = \overline{FL}/\overline{RT} = V_{IH}$	T -		10	mA
Standby Power Supply Current	I _{SB}	All Inputs $\geq V_{CC} - 0.2V$ or $\leq V_{CC}$	_		1	mA
Output High Voltage	V _{OH}	$I_{OH} = -4mA$	2.4	_	_	V
Output Low Voltage	V _{OL}	I _{OL} = 8mA	_	_	0.4	V

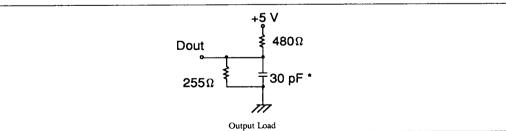
EXECUTANCE $(T_a = 25^{\circ}C, f = 1MHz)$

Parameter	Symbol	Test Conditions	Тур.	Max.	Unit
Input Capacitance	C _{in}	$V_{in} = 0V$	_	TBD	pF
Output Capacitance	Cout	$V_{out} = 0V$	_	TBD	pF

M AC CHARACTERISTICS ($T_a = 0$ °C to 70°C, $V_{CC} = 5 \pm 10\%$)

Test Conditions

- Input Pulse Levels: VSS to 3.0V
- Input and Output Timing Reference Level: 1.5V
- Input Rise and Fall Times: 5ns
- Output Load: See Figure



^{*}Including scope and jig.

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• Read Cycle

Parameter	Symbol	HM63941-25		HM63941-35		HM63941-45		Unit
rarameter	Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit
Read Cycle Time	t _{RC}	35	_	45		60		ns
Access Time	t _A		25		35		45	ns
Read Recovery Time	t _{RR}	10		10		15	1 –	ns
Read Pulse Width	t _{RPW}	25		35	_	45	T —	ns
Read Low to DB Low Z	t _{RLZ}	5	_	5		10	-	ns
Read High to DB High Z	t _{RHZ}	_	15		20	_	25	ns
Data Valid from Read High	t _{OH}	5		5		5		ns

• Write Cycle

Parameter	Symbol	HM63941-25		HM63941-35		HM63941-45		Unit
r at attletet		Min.	Max.	Min.	Max.	Min.	Max.	Unit
Write Cycle Time	t _{WC}	35	_	45	_	60	_	ns
Write Recovery Time	twR	10	_	10		15	_	ns
Write Pulse Width	t _{WPW}	20	-	35		45	_	ns
Data Setup Time	t _{DS}	15	T -	20	_	25		ns
Data Hold Time	t _{DH}	0	_	0		5	_	ns

• Reset Cycle

Parameter	Symbol	HM63941-25		HM63941-35		HM63941-45		11-14
	Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit
Reset Cycle Time	t _{RSC}	35	_	45	-	60		ns
Reset Pulse Width	t _{RS}	25	_	35	_	45	-	ns
Reset Recovery Time	t _{RSR}	10		10	_	15	1	ns

• Retransmit Cycle

Parameter	Symbol	HM63941-25		HM63941-35		HM63941-45		T T=iA
Farameter	Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit
Retransmit Cycle Time	t _{RTC}	35		45	_	60	_	ns
Retransmit Pulse Width	t _{RT}	20	_	35		45		ns
Retransmit Recovery Time	t _{RTR}	10		10	_	15		ns

• Flag Timing

Parameter	Symphol	HM63941-25		HM63941-35		HM63941-45		Unit
Farameter	Symbol	Min.	Max.	Min.	Max.	Min.	Max.	Unit
Reset to Empty Flag Low	t _{EFL}	_	30		45		60	ns
Read Low to Empty Flag Low	t _{REF}		25		35		45	ns
Read High to Full Flag High	t _{RFF}	_	25	_	35	_	45	ns
Write High to Empty Flag High	tweF	_	25	_	35		45	ns
Write Low to Full Flag Low	t _{WFF}	_	25		35	_	45	ns
Write Low to Almost-Full Low	t _{WAF}		30	_	40	_	55	ns
Read High to Almost-Full High	t _{RAF}		30		40	_	55	ns

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SIGNAL DESCRIPTIONS

Inputs

• Reset (RS)

The device is reset whenever \overline{RS} input is taken to low state, for minimum reset pulse width. When device is reset, both read and write pointers are set to the first location. A reset cycle is required after power on. Both read enable (\overline{R}) and write enable (\overline{W}) inputs must be in the high state during reset. Empty flag (\overline{EF}) will go low and full flag (\overline{FF}) and almost-full (\overline{AF}) will go high during reset cycle.

Write enable (W)
 Write cycle is initiated at the falling edge of W, if the full flag (FF) is not set, provided that data set-up and hold time requirements relative to the rising edge of (W) are met. Data is stored in the device sequentially and independently of any simultaneous read operation. To inhibit further write operations and prevent internal data overflow full flag (FF) will go low.

• Read enable (R) Read cycle is initiated at the falling edge of R, if the empty flag (EF) is not set. Data is accessed on a first-in, first-out basis independently of simultaneous write operation. As read enable (R) goes high, all outputs will return to high impedance state, till next read operation. After the last data has been read from the FIFO, the empty flag (EF) will go low, preventing further read operations with output kept in high impedance state. Empty flag (EF) will go high during a valid write cycle (t_{WEF}), thereafter a valid read can start.

First load/retransmit (FL/RT)
 For depth expansion mode, this pin is grounded to indicate that it is the first device, while this pin of the rest of devices should connect to V_{CC} for correct operation. In single device mode, this pin resets the read pointer to the beginning of the FIFO memory, therefore data can be reread from the beginning. Both R and W should be kept high while RT is taken low.

Expansion-in (XI)
 For single device mode expansion-in (XI) is grounded. For depth expansion mode, expansion-in (XI) should be connected to expansion-out (XO) of previous device.

Data In (D₀ to D₈)
 Data inputs for 9-bit wide data.

Outputs

Full Flag (FF)
 The full flag (FF) will go low when FIFO is full, inhibiting further write operations until one or more read operations are completed or the FIFO is reset.

Empty flag (EF)
 The empty flag (EF) will go low when the FIFO becomes empty, inhibiting further read opera-

tions, until one or more write operations are completed, or FIFO is set to retransmit.

• Expansion-out (XO)/Almost-full flag (ĀF) This output has dual functionality depending how it is used. In depth expansion configuration expansion-out (XO) is connected to next expansion-in (XI). The expansion-out (XO) of the last FIFO is connected to the expansion-in (XI) of the first FIFO. In this way the first FIFO indicates the next FIFO that it will receive the next data. In like manner, any FIFO which becomes full will indicate the next FIFO that it will receive the next data. The second function of this output is in stand alone and/or parallel expansion configurations to indicate the system user that the FIFO is almost full.

• Data outputs $(Q_0$ to $Q_8)$ Data outputs for 9-bit wide data. These outputs are in high impedance state when \overline{R} is in high state.

VARIOUS OPERATIONS MODE

- Single device mode
 If only one FIFO is used, the expansion-in (XI) pin should be grounded.
- Width expansion mode
 Width expansion by 9-bit increments may be achieved when separately paralleling the data inputs and the data outputs. In this configuration any flags of any device may be used. To avoid output contention of the flags for short periods of time, the flag outputs should not be wired together.
- Depth expansion mode Multiple of FIFOs could provide multiple of 4k x 9 as (N) x (4k) by 9-bits wide, where N is the number of FIFOs connected in depth expansion mode

The following arrangement must be provided.

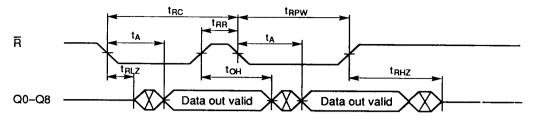
- First load (FL) of the first FIFO should be connected to ground.
- 2. All other (FL) should be connected to V_{CC}.
- Connect the expansion-out (XO) of each FIFO to expansion-in (XI) of the next FIFO serially and XO of the last FIFO to XI of the first FIFO.
- Connect all the empty flag (EF) together to OR gate and connect all the full flag (FF) together to OR gate to obtain two separate valid empty flag (EF) and full flag (FF) outputs.
- 5. (RT) and (AF) will not be available in this mode.
- Compound expansion mode
 Combination of width and depth expansion modes will provide larger FIFO arrays.



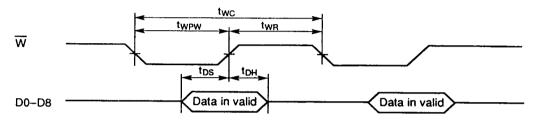
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TIMING WAVEFORM

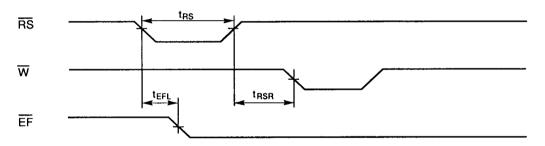
• Read Cycle



• Write Cycle



• Reset Cycle

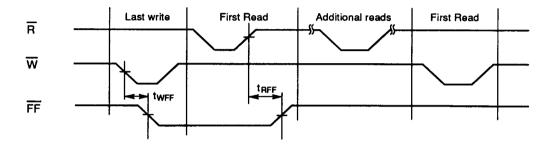


NOTES:

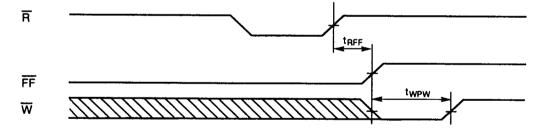
- 1. $\overline{W} = \overline{R} = V_{IH}$ during reset.
- 2. $t_{RSC} = t_{RST}$, t_{RSR} .

t_{RTR}

• Full-Flag Cycle (From Last Write to First Read)

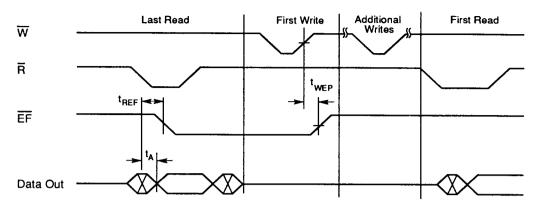


• Full-Flag Cycle (Effective Write Pulse Width After FF High)

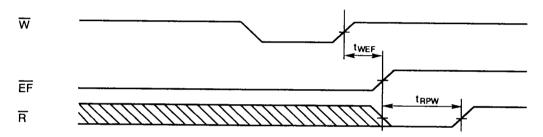


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• Empty-Flag Cycle (Effective Read Pulse Width After EF High)



• Almost-Full Flag Cycle

